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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	120
Number of Logic Elements/Cells	1200
Total RAM Bits	24576
Number of I/O	-
Number of Gates	113000
Voltage - Supply	1.71V ~ 1.89V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	256-LBGA
Supplier Device Package	256-BGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep20k30efc256-1

- Flexible clock management circuitry with up to four phase-locked loops (PLLs)
  - Built-in low-skew clock tree
  - Up to eight global clock signals
  - ClockLock® feature reducing clock delay and skew
  - ClockBoost® feature providing clock multiplication and division
  - ClockShift™ programmable clock phase and delay shifting
- Powerful I/O features
  - Compliant with peripheral component interconnect Special Interest Group (PCI SIG) ***PCI Local Bus Specification, Revision 2.2*** for 3.3-V operation at 33 or 66 MHz and 32 or 64 bits
  - Support for high-speed external memories, including DDR SDRAM and ZBT SRAM (ZBT is a trademark of Integrated Device Technology, Inc.)
  - Bidirectional I/O performance (t_{CO} + t_{SU}) up to 250 MHz
  - LVDS performance up to 840 Mbits per channel
  - Direct connection from I/O pins to local interconnect providing fast t_{CO} and t_{SU} times for complex logic
  - MultiVolt I/O interface support to interface with 1.8-V, 2.5-V, 3.3-V, and 5.0-V devices (see Table 3)
  - Programmable clamp to V_{CCIO}
  - Individual tri-state output enable control for each pin
  - Programmable output slew-rate control to reduce switching noise
  - Support for advanced I/O standards, including low-voltage differential signaling (LVDS), LVPECL, PCI-X, AGP, CTT, stub-series terminated logic (SSTL-3 and SSTL-2), Gunning transceiver logic plus (GTL+), and high-speed terminated logic (HSTL Class I)
  - Pull-up on I/O pins before and during configuration
- Advanced interconnect structure
  - Four-level hierarchical FastTrack® Interconnect structure providing fast, predictable interconnect delays
  - Dedicated carry chain that implements arithmetic functions such as fast adders, counters, and comparators (automatically used by software tools and megafunctions)
  - Dedicated cascade chain that implements high-speed, high-fan-in logic functions (automatically used by software tools and megafunctions)
  - Interleaved local interconnect allows one LE to drive 29 other LEs through the fast local interconnect
- Advanced packaging options
  - Available in a variety of packages with 144 to 1,020 pins (see Tables 4 through 7)
  - FineLine BGA® packages maximize board space efficiency
- Advanced software support
  - Software design support and automatic place-and-route provided by the Altera® Quartus® II development system for

Windows-based PCs, Sun SPARCstations, and HP 9000 Series 700/800 workstations
- Altera MegaCore® functions and Altera Megafunction Partners Program (AMPP℠) megafunctions
- NativeLink™ integration with popular synthesis, simulation, and timing analysis tools
- Quartus II SignalTap® embedded logic analyzer simplifies in-system design evaluation by giving access to internal nodes during device operation
- Supports popular revision-control software packages including PVCS, Revision Control System (RCS), and Source Code Control System (SCCS)

Table 4. APEX 20K QFP, BGA & PGA Package Options & I/O Count *Notes (1), (2)*

Device	144-Pin TQFP	208-Pin PQFP RQFP	240-Pin PQFP RQFP	356-Pin BGA	652-Pin BGA	655-Pin PGA
EP20K30E	92	125				
EP20K60E	92	148	151	196		
EP20K100	101	159	189	252		
EP20K100E	92	151	183	246		
EP20K160E	88	143	175	271		
EP20K200		144	174	277		
EP20K200E		136	168	271	376	
EP20K300E			152		408	
EP20K400					502	502
EP20K400E					488	
EP20K600E					488	
EP20K1000E					488	
EP20K1500E					488	

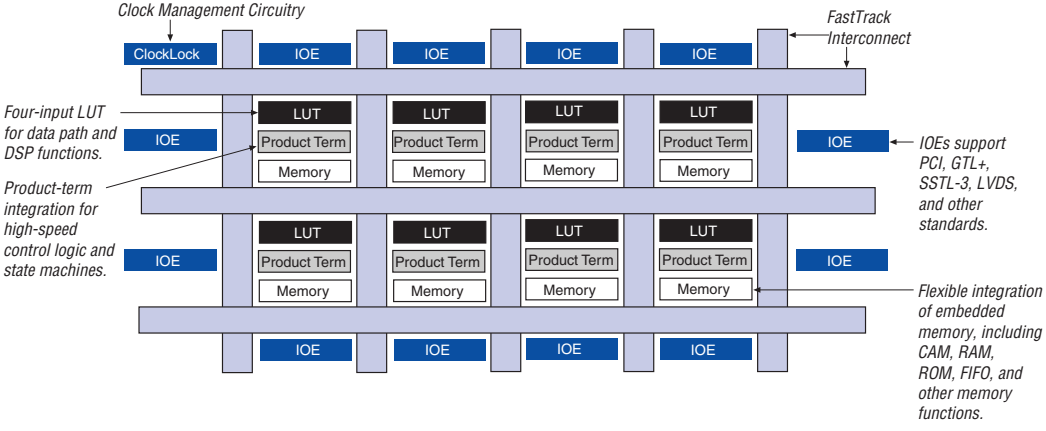
Functional Description

APEX 20K devices incorporate LUT-based logic, product-term-based logic, and memory into one device. Signal interconnections within APEX 20K devices (as well as to and from device pins) are provided by the FastTrack® Interconnect—a series of fast, continuous row and column channels that run the entire length and width of the device.

Each I/O pin is fed by an I/O element (IOE) located at the end of each row and column of the FastTrack Interconnect. Each IOE contains a bidirectional I/O buffer and a register that can be used as either an input or output register to feed input, output, or bidirectional signals. When used with a dedicated clock pin, these registers provide exceptional performance. IOEs provide a variety of features, such as 3.3-V, 64-bit, 66-MHz PCI compliance; JTAG BST support; slew-rate control; and tri-state buffers. APEX 20KE devices offer enhanced I/O support, including support for 1.8-V I/O, 2.5-V I/O, LVCMOS, LVTTL, LVPECL, 3.3-V PCI, PCI-X, LVDS, GTL+, SSTL-2, SSTL-3, HSTL, CTT, and 3.3-V AGP I/O standards.

The ESB can implement a variety of memory functions, including CAM, RAM, dual-port RAM, ROM, and FIFO functions. Embedding the memory directly into the die improves performance and reduces die area compared to distributed-RAM implementations. Moreover, the abundance of cascadable ESBs ensures that the APEX 20K device can implement multiple wide memory blocks for high-density designs. The ESB's high speed ensures it can implement small memory blocks without any speed penalty. The abundance of ESBs ensures that designers can create as many different-sized memory blocks as the system requires. Figure 1 shows an overview of the APEX 20K device.

Figure 1. APEX 20K Device Block Diagram

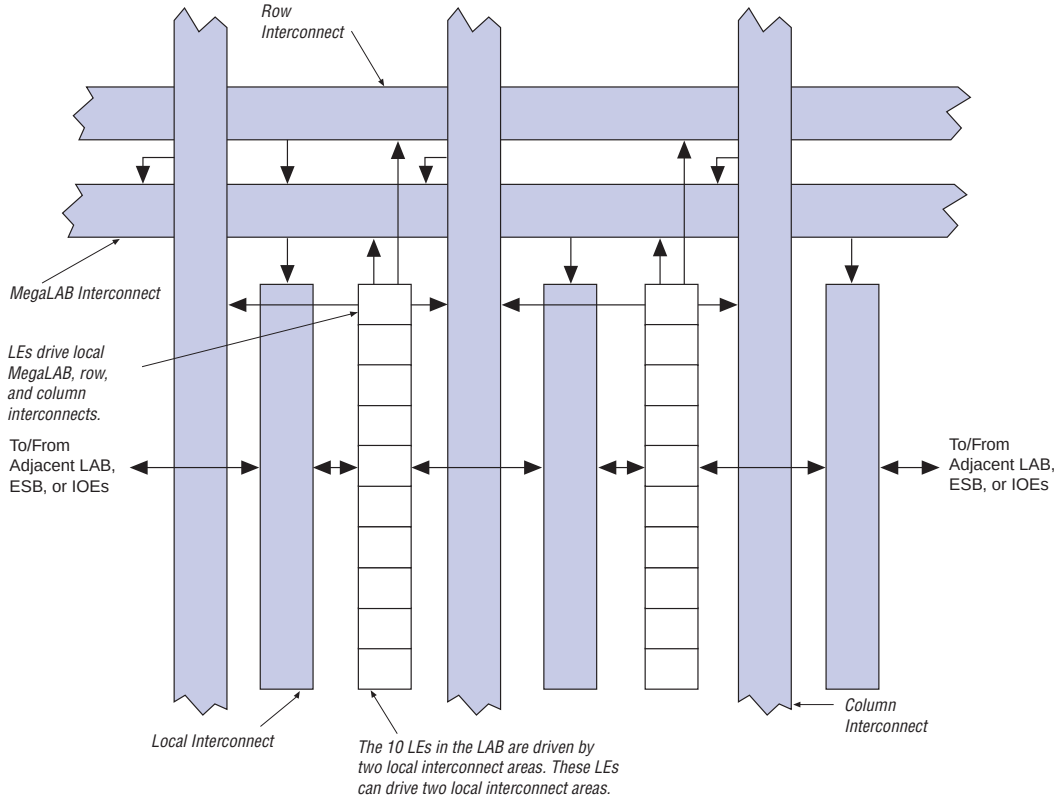


Logic Array Block

Each LAB consists of 10 LEs, the LEs' associated carry and cascade chains, LAB control signals, and the local interconnect. The local interconnect transfers signals between LEs in the same or adjacent LABs, IOEs, or ESBs. The Quartus II Compiler places associated logic within an LAB or adjacent LABs, allowing the use of a fast local interconnect for high performance. Figure 3 shows the APEX 20K LAB.

APEX 20K devices use an interleaved LAB structure. This structure allows each LE to drive two local interconnect areas. This feature minimizes use of the MegaLAB and FastTrack interconnect, providing higher performance and flexibility. Each LE can drive 29 other LEs through the fast local interconnect.

Figure 3. LAB Structure



Each LE has two outputs that drive the local, MegaLAB, or FastTrack Interconnect routing structure. Each output can be driven independently by the LUT's or register's output. For example, the LUT can drive one output while the register drives the other output. This feature, called register packing, improves device utilization because the register and the LUT can be used for unrelated functions. The LE can also drive out registered and unregistered versions of the LUT output.

The APEX 20K architecture provides two types of dedicated high-speed data paths that connect adjacent LEs without using local interconnect paths: carry chains and cascade chains. A carry chain supports high-speed arithmetic functions such as counters and adders, while a cascade chain implements wide-input functions such as equality comparators with minimum delay. Carry and cascade chains connect LEs 1 through 10 in an LAB and all LABs in the same MegaLAB structure.

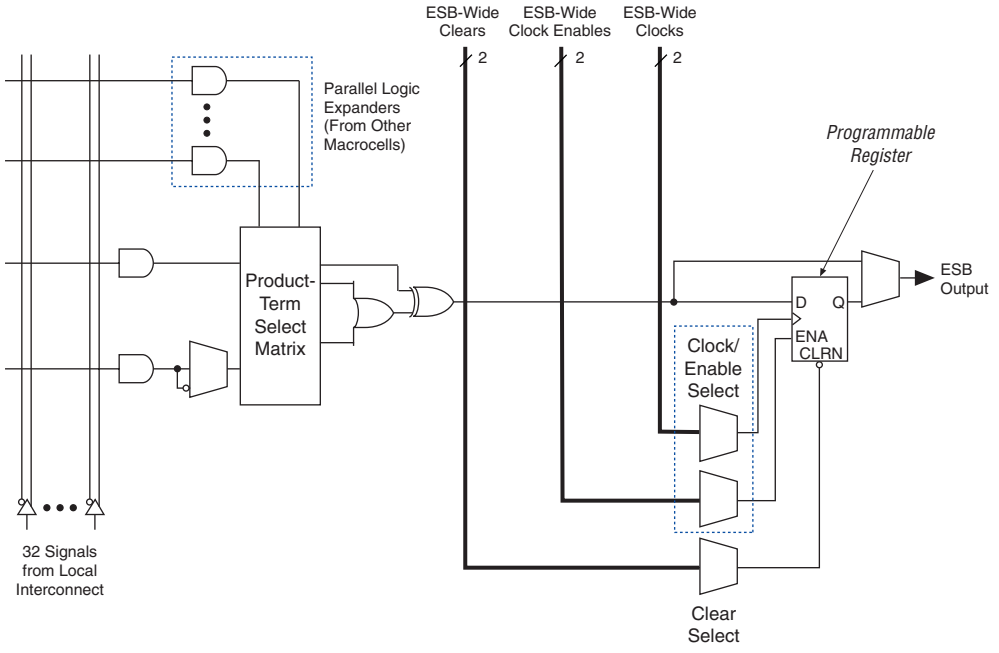
Carry Chain

The carry chain provides a very fast carry-forward function between LEs. The carry-in signal from a lower-order bit drives forward into the higher-order bit via the carry chain, and feeds into both the LUT and the next portion of the carry chain. This feature allows the APEX 20K architecture to implement high-speed counters, adders, and comparators of arbitrary width. Carry chain logic can be created automatically by the Quartus II software Compiler during design processing, or manually by the designer during design entry. Parameterized functions such as library of parameterized modules (LPM) and DesignWare functions automatically take advantage of carry chains for the appropriate functions.

The Quartus II software Compiler creates carry chains longer than ten LEs by linking LABs together automatically. For enhanced fitting, a long carry chain skips alternate LABs in a MegaLAB™ structure. A carry chain longer than one LAB skips either from an even-numbered LAB to the next even-numbered LAB, or from an odd-numbered LAB to the next odd-numbered LAB. For example, the last LE of the first LAB in the upper-left MegaLAB structure carries to the first LE of the third LAB in the MegaLAB structure.

Figure 6 shows how an *n*-bit full adder can be implemented in *n* + 1 LEs with the carry chain. One portion of the LUT generates the sum of two bits using the input signals and the carry-in signal; the sum is routed to the output of the LE. The register can be bypassed for simple adders or used for accumulator functions. Another portion of the LUT and the carry chain logic generates the carry-out signal, which is routed directly to the carry-in signal of the next-higher-order bit. The final carry-out signal is routed to an LE, where it is driven onto the local, MegaLAB, or FastTrack Interconnect routing structures.

Figure 14. APEX 20K Macrocell

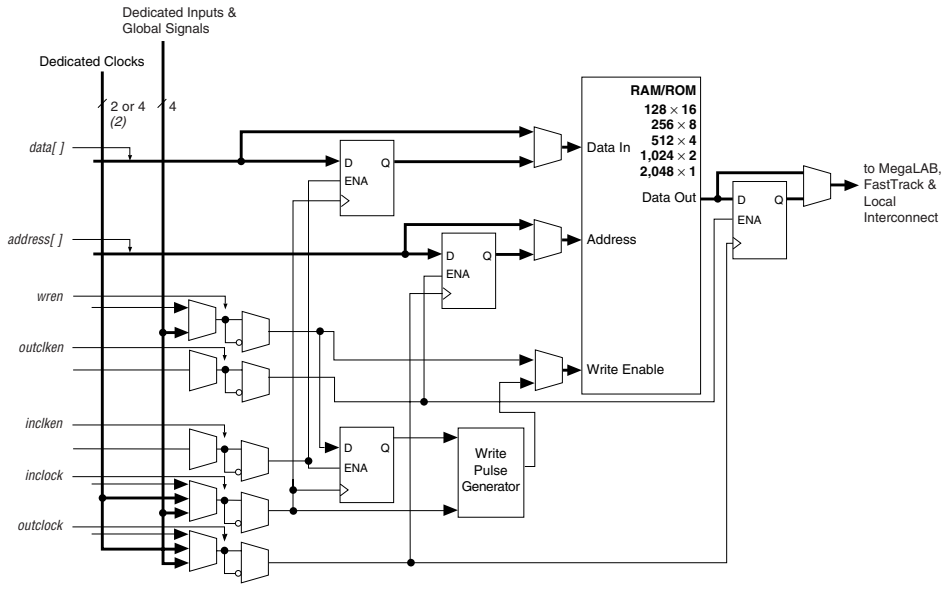


For registered functions, each macrocell register can be programmed individually to implement D, T, JK, or SR operation with programmable clock control. The register can be bypassed for combinatorial operation. During design entry, the designer specifies the desired register type; the Quartus II software then selects the most efficient register operation for each registered function to optimize resource utilization. The Quartus II software or other synthesis tools can also select the most efficient register operation automatically when synthesizing HDL designs.

Each programmable register can be clocked by one of two ESB-wide clocks. The ESB-wide clocks can be generated from device dedicated clock pins, global signals, or local interconnect. Each clock also has an associated clock enable, generated from the local interconnect. The clock and clock enable signals are related for a particular ESB; any macrocell using a clock also uses the associated clock enable.

If both the rising and falling edges of a clock are used in an ESB, both ESB-wide clock signals are used.

Figure 22. ESB in Single-Port Mode *Note (1)*



Notes to Figure 22:

(1) All registers can be asynchronously cleared by ESB local interconnect signals, global signals, or the chip-wide reset.
(2) APEX 20KE devices have four dedicated clocks.

Content-Addressable Memory

In APEX 20KE devices, the ESB can implement CAM. CAM can be thought of as the inverse of RAM. When read, RAM outputs the data for a given address. Conversely, CAM outputs an address for a given data word. For example, if the data `FA12` is stored in address `14`, the CAM outputs `14` when `FA12` is driven into it.

CAM is used for high-speed search operations. When searching for data within a RAM block, the search is performed serially. Thus, finding a particular data word can take many cycles. CAM searches all addresses in parallel and outputs the address storing a particular word. When a match is found, a match flag is set high. Figure 23 shows the CAM block diagram.

Table 22 shows the JTAG timing parameters and values for APEX 20K devices.

Table 22. APEX 20K JTAG Timing Parameters & Values

Symbol	Parameter	Min	Max	Unit
t_{JCP}	TCK clock period	100		ns
t_{JCH}	TCK clock high time	50		ns
t_{JCL}	TCK clock low time	50		ns
t_{JPSU}	JTAG port setup time	20		ns
t_{JPH}	JTAG port hold time	45		ns
t_{JPCO}	JTAG port clock to output		25	ns
t_{JPZX}	JTAG port high impedance to valid output		25	ns
t_{JPXZ}	JTAG port valid output to high impedance		25	ns
t_{JSSU}	Capture register setup time	20		ns
t_{JSH}	Capture register hold time	45		ns
t_{JSCO}	Update register clock to output		35	ns
t_{JSZX}	Update register high impedance to valid output		35	ns
t_{JSXZ}	Update register valid output to high impedance		35	ns

For more information, see the following documents:

- *Application Note 39 (IEEE Std. 1149.1 (JTAG) Boundary-Scan Testing in Altera Devices)*
- *Jam Programming & Test Language Specification*

Generic Testing

Each APEX 20K device is functionally tested. Complete testing of each configurable static random access memory (SRAM) bit and all logic functionality ensures 100% yield. AC test measurements for APEX 20K devices are made under conditions equivalent to those shown in Figure 32. Multiple test patterns can be used to configure devices during all stages of the production flow.

Table 25. APEX 20K 5.0-V Tolerant Device DC Operating Conditions (Part 2 of 2) *Notes (2), (7), (8)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{OL}	3.3-V low-level TTL output voltage	I_{OL} = 12 mA DC, V_{CCIO} = 3.00 V *(11)*			0.45	V
	3.3-V low-level CMOS output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 3.00 V *(11)*			0.2	V
	3.3-V low-level PCI output voltage	I_{OL} = 1.5 mA DC, V_{CCIO} = 3.00 to 3.60 V *(11)*			$0.1 \times V_{CCIO}$	V
	2.5-V low-level output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 2.30 V *(11)*			0.2	V
		I_{OL} = 1 mA DC, V_{CCIO} = 2.30 V *(11)*			0.4	V
		I_{OL} = 2 mA DC, V_{CCIO} = 2.30 V *(11)*			0.7	V
I_I	Input pin leakage current	V_I = 5.75 to –0.5 V	–10		10	µA
I_{OZ}	Tri-stated I/O pin leakage current	V_O = 5.75 to –0.5 V	–10		10	µA
I_{CC0}	V_{CC} supply current (standby) (All ESBs in power-down mode)	V_I = ground, no load, no toggling inputs, -1 speed grade *(12)*		10		mA
		V_I = ground, no load, no toggling inputs, -2, -3 speed grades *(12)*		5		mA
R_{CONF}	Value of I/O pin pull-up resistor before and during configuration	V_{CCIO} = 3.0 V *(13)*	20		50	W
		V_{CCIO} = 2.375 V *(13)*	30		80	W

Table 29. APEX 20KE Device DC Operating Conditions *Notes (7), (8), (9)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IH}	High-level LVTTL, CMOS, or 3.3-V PCI input voltage		1.7, 0.5 × V_{CCIO} *(10)*		4.1	V
V_{IL}	Low-level LVTTL, CMOS, or 3.3-V PCI input voltage		–0.5		0.8, 0.3 × V_{CCIO} *(10)*	V
V_{OH}	3.3-V high-level LVTTL output voltage	I_{OH} = –12 mA DC, V_{CCIO} = 3.00 V *(11)*	2.4			V
	3.3-V high-level LVCMOS output voltage	I_{OH} = –0.1 mA DC, V_{CCIO} = 3.00 V *(11)*	V_{CCIO} – 0.2			V
	3.3-V high-level PCI output voltage	I_{OH} = –0.5 mA DC, V_{CCIO} = 3.00 to 3.60 V *(11)*	0.9 × V_{CCIO}			V
	2.5-V high-level output voltage	I_{OH} = –0.1 mA DC, V_{CCIO} = 2.30 V *(11)*	2.1			V
		I_{OH} = –1 mA DC, V_{CCIO} = 2.30 V *(11)*	2.0			V
		I_{OH} = –2 mA DC, V_{CCIO} = 2.30 V *(11)*	1.7			V
V_{OL}	3.3-V low-level LVTTL output voltage	I_{OL} = 12 mA DC, V_{CCIO} = 3.00 V *(12)*			0.4	V
	3.3-V low-level LVCMOS output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 3.00 V *(12)*			0.2	V
	3.3-V low-level PCI output voltage	I_{OL} = 1.5 mA DC, V_{CCIO} = 3.00 to 3.60 V *(12)*			0.1 × V_{CCIO}	V
	2.5-V low-level output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 2.30 V *(12)*			0.2	V
		I_{OL} = 1 mA DC, V_{CCIO} = 2.30 V *(12)*			0.4	V
		I_{OL} = 2 mA DC, V_{CCIO} = 2.30 V *(12)*			0.7	V
I_I	Input pin leakage current	V_I = 4.1 to –0.5 V *(13)*	–10		10	µA
I_{OZ}	Tri-stated I/O pin leakage current	V_O = 4.1 to –0.5 V *(13)*	–10		10	µA
I_{CC0}	V_{CC} supply current (standby) (All ESBs in power-down mode)	V_I = ground, no load, no toggling inputs, -1 speed grade		10		mA
		V_I = ground, no load, no toggling inputs, -2, -3 speed grades		5		mA
R_{CONF}	Value of I/O pin pull-up resistor before and during configuration	V_{CCIO} = 3.0 V *(14)*	20		50	kΩ
		V_{CCIO} = 2.375 V *(14)*	30		80	kΩ
		V_{CCIO} = 1.71 V *(14)*	60		150	kΩ

For DC Operating Specifications on APEX 20KE I/O standards, please refer to *Application Note 117 (Using Selectable I/O Standards in Altera Devices).*

Table 30. APEX 20KE Device Capacitance *Note (15)*

Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	V_{IN} = 0 V, f = 1.0 MHz		8	pF
C_{INCLK}	Input capacitance on dedicated clock pin	V_{IN} = 0 V, f = 1.0 MHz		12	pF
C_{OUT}	Output capacitance	V_{OUT} = 0 V, f = 1.0 MHz		8	pF

Notes to Tables 27 through 30:

(1) See the *Operating Requirements for Altera Devices Data Sheet*.
(2) Minimum DC input is –0.5 V. During transitions, the inputs may undershoot to –2.0 V or overshoot to 5.75 V for input currents less than 100 mA and periods shorter than 20 ns.
(3) Numbers in parentheses are for industrial-temperature-range devices.
(4) Maximum V_{CC} rise time is 100 ms, and V_{CC} must rise monotonically.
(5) Minimum DC input is –0.5 V. During transitions, the inputs may undershoot to –2.0 V or overshoot to the voltage shown in the following table based on input duty cycle for input currents less than 100 mA. The overshoot is dependent upon duty cycle of the signal. The DC case is equivalent to 100% duty cycle.

Vin	Max. Duty Cycle
4.0V	100% (DC)
4.1	90%
4.2	50%
4.3	30%
4.4	17%
4.5	10%

(6) All pins, including dedicated inputs, clock, I/O, and JTAG pins, may be driven before V_{CCINT} and V_{CCIO} are powered.
(7) Typical values are for T_A = 25° C, V_{CCINT} = 1.8 V, and V_{CCIO} = 1.8 V, 2.5 V or 3.3 V.
(8) These values are specified under the APEX 20KE device recommended operating conditions, shown in Table 24 on page 60.
(9) Refer to *Application Note 117 (Using Selectable I/O Standards in Altera Devices)* for the V_{IH}, V_{IL}, V_{OH}, V_{OL}, and I_I parameters when VCCIO = 1.8 V.
(10) The APEX 20KE input buffers are compatible with 1.8-V, 2.5-V and 3.3-V (LVTTL and LVCMOS) signals. Additionally, the input buffers are 3.3-V PCI compliant. Input buffers also meet specifications for GTL+, CTT, AGP, SSTL-2, SSTL-3, and HSTL.
(11) The I_{OH} parameter refers to high-level TTL, PCI, or CMOS output current.
(12) The I_{OL} parameter refers to low-level TTL, PCI, or CMOS output current. This parameter applies to open-drain pins as well as output pins.
(13) This value is specified for normal device operation. The value may vary during power-up.
(14) Pin pull-up resistance values will be lower if an external source drives the pin higher than V_{CCIO}.
(15) Capacitance is sample-tested only.

Figure 33 shows the relationship between V_{CCIO} and V_{CCINT} for 3.3-V PCI compliance on APEX 20K devices.

Figure 37. APEX 20KE f_{MAX} Timing Model

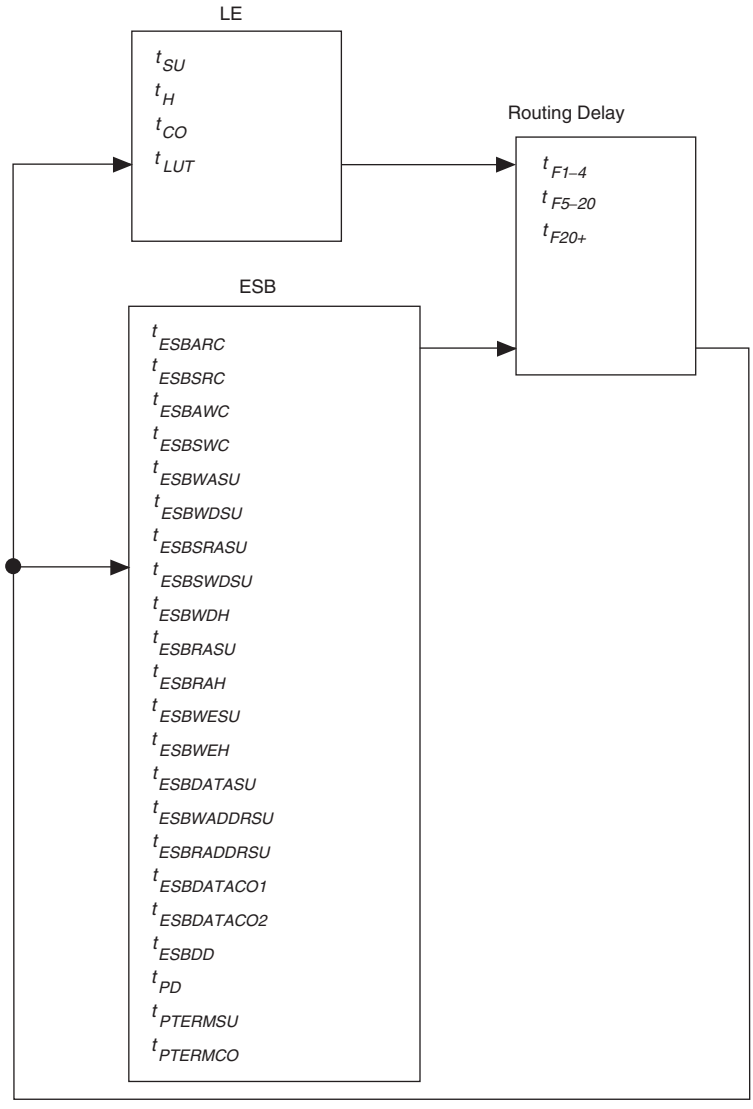
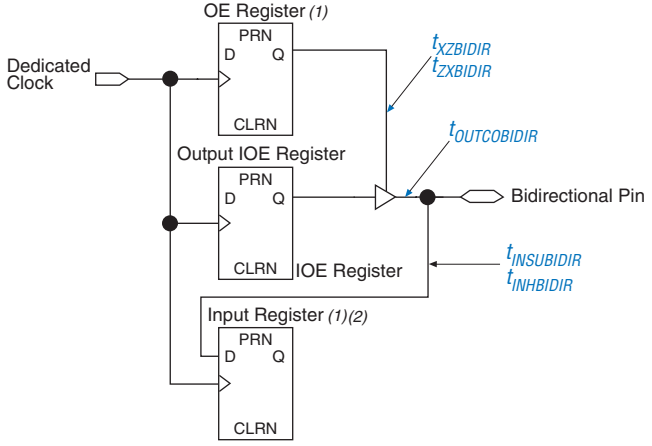


Figure 40. Synchronous Bidirectional Pin External Timing



Notes to Figure 40:

(1) The output enable and input registers are LE registers in the LAB adjacent to a bidirectional row pin. The output enable register is set with "Output Enable Routing= Signal-Pin" option in the Quartus II software.

(2) The LAB adjacent input register is set with "Decrease Input Delay to Internal Cells= Off". This maintains a zero hold time for lab adjacent registers while giving a fast, position independent setup time. A faster setup time with zero hold time is possible by setting "Decrease Input Delay to Internal Cells= ON" and moving the input register farther away from the bidirectional pin. The exact position where zero hold occurs with the minimum setup time, varies with device density and speed grade.

Table 31 describes the f_{MAX} timing parameters shown in Figure 36 on page 68.

Table 31. APEX 20K f_{MAX} Timing Parameters (Part 1 of 2)

Symbol	Parameter
t_{SU}	LE register setup time before clock
t_{H}	LE register hold time after clock
t_{CO}	LE register clock-to-output delay
t_{LUT}	LUT delay for data-in
t_{ESBRC}	ESB Asynchronous read cycle time
t_{ESBWC}	ESB Asynchronous write cycle time
$t_{ESBWESU}$	ESB WE setup time before clock when using input register
$t_{ESBDATASU}$	ESB data setup time before clock when using input register
$t_{ESBDATAH}$	ESB data hold time after clock when using input register
$t_{ESBADDRSU}$	ESB address setup time before clock when using input registers
$t_{ESBDATACO1}$	ESB clock-to-output delay when using output registers

Notes to Tables 43 through 48:
(1) This parameter is measured without using ClockLock or ClockBoost circuits.
(2) This parameter is measured using ClockLock or ClockBoost circuits.

Tables 49 through 54 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K30E APEX 20KE devices.

Table 49. EP20K30E f_{MAX} LE Timing Microparameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.01		0.02		0.02		ns
t_{H}	0.11		0.16		0.23		ns
t_{CO}		0.32		0.45		0.67	ns
t_{LUT}		0.85		1.20		1.77	ns

Tables 55 through 60 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K60E APEX 20KE devices.

Table 55. EP20K60E f_{MAX} LE Timing Microparameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.17		0.15		0.16		ns
t_{H}	0.32		0.33		0.39		ns
t_{CO}		0.29		0.40		0.60	ns
t_{LUT}		0.77		1.07		1.59	ns

Table 78. EP20K200E External Bidirectional Timing Parameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	2.81		3.19		3.54		ns
$t_{INHBIDIR}$	0.00		0.00		0.00		ns
$t_{OUTCOBIDIR}$	2.00	5.12	2.00	5.62	2.00	6.11	ns
$t_{XZBIDIR}$		7.51		8.32		8.67	ns
$t_{ZXBIDIR}$		7.51		8.32		8.67	ns
$t_{INSUBIDIRPLL}$	3.30		3.64		-		ns
$t_{INHBIDIRPLL}$	0.00		0.00		-		ns
$t_{OUTCOBIDIRPLL}$	0.50	3.01	0.50	3.36	-	-	ns
$t_{XZBIDIRPLL}$		5.40		6.05		-	ns
$t_{ZXBIDIRPLL}$		5.40		6.05		-	ns

Tables 79 through 84 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K300E APEX 20KE devices.

Table 79. EP20K300E f_{MAX} LE Timing Microparameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.16		0.17		0.18		ns
t_{H}	0.31		0.33		0.38		ns
t_{CO}		0.28		0.38		0.51	ns
t_{LUT}		0.79		1.07		1.43	ns

Table 82. EP20K300E Minimum Pulse Width Timing Parameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{CH}	1.25		1.43		1.67		ns
t_{CL}	1.25		1.43		1.67		ns
t_{CLRP}	0.19		0.26		0.35		ns
t_{PREP}	0.19		0.26		0.35		ns
t_{ESBCH}	1.25		1.43		1.67		ns
t_{ESBCL}	1.25		1.43		1.67		ns
t_{ESBWP}	1.25		1.71		2.28		ns
t_{ESBRP}	1.01		1.38		1.84		ns

Table 83. EP20K300E External Timing Parameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.31		2.44		2.57		ns
t_{INH}	0.00		0.00		0.00		ns
t_{OUTCO}	2.00	5.29	2.00	5.82	2.00	6.24	ns
$t_{INSUPLL}$	1.76		1.85		-		ns
t_{INHPLL}	0.00		0.00		-		ns
$t_{OUTCOPLL}$	0.50	2.65	0.50	2.95	-	-	ns

Table 84. EP20K300E External Bidirectional Timing Parameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	2.77		2.85		3.11		ns
$t_{INHBIDIR}$	0.00		0.00		0.00		ns
$t_{OUTCOBIDIR}$	2.00	5.29	2.00	5.82	2.00	6.24	ns
$t_{XZBIDIR}$		7.59		8.30		9.09	ns
$t_{ZXBIDIR}$		7.59		8.30		9.09	ns
$t_{INSUBIDIRPLL}$	2.50		2.76		-		ns
$t_{INHBIDIRPLL}$	0.00		0.00		-		ns
$t_{OUTCOBIDIRPLL}$	0.50	2.65	0.50	2.95	-	-	ns
$t_{XZBIDIRPLL}$		5.00		5.43		-	ns
$t_{ZXBIDIRPLL}$		5.00		5.43		-	ns

Table 92. EP20K600E f_{MAX} ESB Timing Microparameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.67		2.39		3.11	ns
t_{ESBSRC}		2.27		3.07		3.86	ns
t_{ESBAWC}		3.19		4.56		5.93	ns
t_{ESBSWC}		3.51		4.62		5.72	ns
$t_{ESBWASU}$	1.46		2.08		2.70		ns
t_{ESBWAH}	0.00		0.00		0.00		ns
$t_{ESBWDSU}$	1.60		2.29		2.97		ns
t_{ESBWDH}	0.00		0.00		0.00		ns
$t_{ESBRASU}$	1.61		2.30		2.99		ns
t_{ESBRAH}	0.00		0.00		0.00		ns
$t_{ESBWESU}$	1.49		2.30		3.11		ns
t_{ESBWEH}	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	-0.01		0.35		0.71		ns
$t_{ESBDATAH}$	0.13		0.13		0.13		ns
$t_{ESBWADDRSU}$	0.19		0.62		1.06		ns
$t_{ESBRADDRSU}$	0.25		0.71		1.17		ns
$t_{ESBDATACO1}$		1.01		1.19		1.37	ns
$t_{ESBDATACO2}$		2.18		3.12		4.05	ns
t_{ESBDD}		3.19		4.56		5.93	ns
t_{PD}		1.57		2.25		2.92	ns
$t_{PTERMSU}$	0.85		1.43		2.01		ns
$t_{PTERMCO}$		1.03		1.21		1.39	ns

Table 93. EP20K600E f_{MAX} Routing Delays

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{F1-4}		0.22		0.25		0.26	ns
t_{F5-20}		1.26		1.39		1.52	ns
t_{F20+}		3.51		3.88		4.26	ns

Table 110. Selectable I/O Standard Output Delays

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min
LVCMOS		0.00		0.00		0.00	ns
LVTTL		0.00		0.00		0.00	ns
2.5 V		0.00		0.09		0.10	ns
1.8 V		2.49		2.98		3.03	ns
PCI		–0.03		0.17		0.16	ns
GTL+		0.75		0.75		0.76	ns
SSTL-3 Class I		1.39		1.51		1.50	ns
SSTL-3 Class II		1.11		1.23		1.23	ns
SSTL-2 Class I		1.35		1.48		1.47	ns
SSTL-2 Class II		1.00		1.12		1.12	ns
LVDS		–0.48		–0.48		–0.48	ns
CTT		0.00		0.00		0.00	ns
AGP		0.00		0.00		0.00	ns

Power Consumption

To estimate device power consumption, use the interactive power calculator on the Altera web site at **http://www.altera.com**.

Configuration & Operation

The APEX 20K architecture supports several configuration schemes. This section summarizes the device operating modes and available device configuration schemes.

Operating Modes

The APEX architecture uses SRAM configuration elements that require configuration data to be loaded each time the circuit powers up. The process of physically loading the SRAM data into the device is called configuration. During initialization, which occurs immediately after configuration, the device resets registers, enables I/O pins, and begins to operate as a logic device. The I/O pins are tri-stated during power-up, and before and during configuration. Together, the configuration and initialization processes are called *command mode*; normal device operation is called *user mode*.

Before and during device configuration, all I/O pins are pulled to V_{CCIO} by a built-in weak pull-up resistor.

Revision History

The information contained in the *APEX 20K Programmable Logic Device Family Data Sheet* version 5.1 supersedes information published in previous versions.

Version 5.1

APEX 20K Programmable Logic Device Family Data Sheet version 5.1 contains the following changes:

- In version 5.0, the VI input voltage spec was updated in Table 28 on page 63.
- In version 5.0, *Note (5)* to Tables 27 through 30 was revised.
- Added *Note (2)* to Figure 21 on page 33.

Version 5.0

APEX 20K Programmable Logic Device Family Data Sheet version 5.0 contains the following changes:

- Updated Tables 23 through 26. Removed 2.5-V operating condition tables because all APEX 20K devices are now 5.0-V tolerant.
- Updated conditions in Tables 33, 38 and 39.
- Updated data for $t_{ESBDATAH}$ parameter.

Version 4.3

APEX 20K Programmable Logic Device Family Data Sheet version 4.3 contains the following changes:

- Updated Figure 20.
- Updated *Note (2)* to Table 13.
- Updated notes to Tables 27 through 30.

Version 4.2

APEX 20K Programmable Logic Device Family Data Sheet version 4.2 contains the following changes:

- Updated Figure 29.
- Updated *Note (1)* to Figure 29.